L Number	Hits	Search T xt	DB	Time stamp
1	3	(yi-sang-hyun kim-yoʻung-nam).in.	USPAT;	2003/05/02
•	J	W. amid which having wantime	US-PGPUB;	15:01
			IBM_TDB	
2	75	multilayer with metalization	USPAT;	2003/05/02
-	, 3	marriayer with meranzarion	US-PGPUB;	15:02
			IBM_TDB	
3	54	multi-layer with metalization	USPAT;	2003/05/02
3	3.1	man layer will the ranzamen	US-PGPUB;	15:02
			IBM_TDB	
4	204	multiple with metalization	USPAT;	2003/05/02
·	204	marriple with metalization	US-PGPUB;	15:06
			IBM_TDB	13.00
5	321	(multilayer with metalization) (multi-layer with	USPAT;	2003/05/02
,	321	metalization) (multiple with metalization)	US-PGPUB;	15:02
		meralization) (marriple with meralization)	IBM_TDB	15.02
_	15	((multilayer with metalization) (multi-layer with	USPAT;	2003/05/02
6	15	metalization) (multiple with metalization)) and crack?	US-PGPUB;	15:02
		metalization) (multiple with metalization)) and cracks	IBM_TDB	15.02
_	14247	About aliabase	USPAT;	2003/05/02
7	14267	thermal adj stress	US-PGPUB;	15:06
			1	15.06
	0450	12 101 111 111	IBM_TDB	2002/05/02
8	2659	crack? and (thermal adj stress)	USPAT;	2003/05/02
			US-PGPUB;	15:04
		(0.57 1750 750 400 4400) 441 0	IBM_TDB	2002 (05 (02
12	3154	(257/750,758;438/622).CCLS.	USPAT;	2003/05/02
			US-PGPUB;	15:06
	_		IBM_TDB	2002/05/02
13	3	multiple with metalization	EPO; JPO;	2003/05/02
			DERWENT	15:06
14	13917	thermal adj stress	EPO; JPO;	2003/05/02
	:		DERWENT	15:06
15	766	(thermal adj stress) and crack?	EPO; JPO;	2003/05/02
			DERWENT	15:06
16	187	((thermal adj stress) and crack?) and semiconductor	EPO; JPO;	2003/05/02
			DERWENT	15:08
10	225	(crack? and (thermal adj stress)) and 438/\$.ccls.	USPAT;	2003/05/02
,			US-PGPUB;	15:15
			IBM_TDB	
17	162	((crack? and (thermal adj stress)) and 438/\$.ccls.)	USPAT;	2003/05/02
		and @ad<20010220	US-PGPUB;	15:15
			IBM_TDB	